

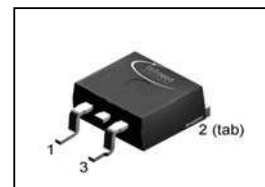
**SIPMOS® Power-Transistor**
**Features**

- P-Channel
- Enhancement mode
- Avalanche rated
- $dv/dt$  rated
- 175°C operating temperature
- Pb-free lead finishing; RoHS compliant

**Product Summary**

$V_{DS}$	-60	V
$R_{DS(on),max}$	0.3	$\Omega$
$I_D$	-8.8	A

PG-TO263-3



Type	Package	Tape and reel information	Marking	Lead free	Packing
SPB08P06PG	PG-TO263-3			Yes	

**Maximum ratings, at  $T_j=25\text{ °C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	Value	Unit
			steady state	
Continuous drain current	$I_D$	$T_A=25\text{ °C}$	-8.8	A
		$T_A=100\text{ °C}$	-6.3	
Pulsed drain current	$I_{D,pulse}$	$T_A=25\text{ °C}$	-35.32	
Avalanche energy, single pulse	$E_{AS}$	$I_D=8.83\text{ A}$ , $R_{GS}=25\ \Omega$	70	mJ
Reverse diode $dv/dt$	$dv/dt$	$I_D=8.83\text{ A}$ , $V_{DS}=48\text{ V}$ , $di/dt=-200\text{ A}/\mu\text{s}$ , $T_{j,max}=175\text{ °C}$	-6	kV/ $\mu\text{s}$
Gate source voltage	$V_{GS}$		$\pm 20$	V
Power dissipation	$P_{tot}$	$T_A=25\text{ °C}$	42	W
Operating and storage temperature	$T_j$ , $T_{stg}$		"-55 ... +175"	$^{\circ}\text{C}$
ESD class				
Soldering temperature			260 $^{\circ}\text{C}$	
IEC climatic category; DIN IEC 68-1			55/150/56	